

HSC285

Silicon Schottky Barrier Diode for High frequency detection

REJ03G0011-0100Z Rev.1.00 Apr.16.2003

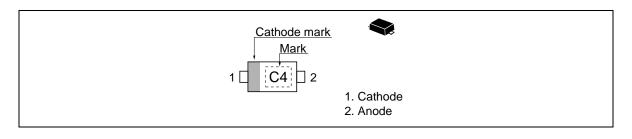
Features

- Low forward voltage, Low capacitance and High detection sensitivity.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HSC285	C4	UFP

Pin Arrangement



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Reverse voltage	V_R	2	V
Average rectified current	Io	5	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

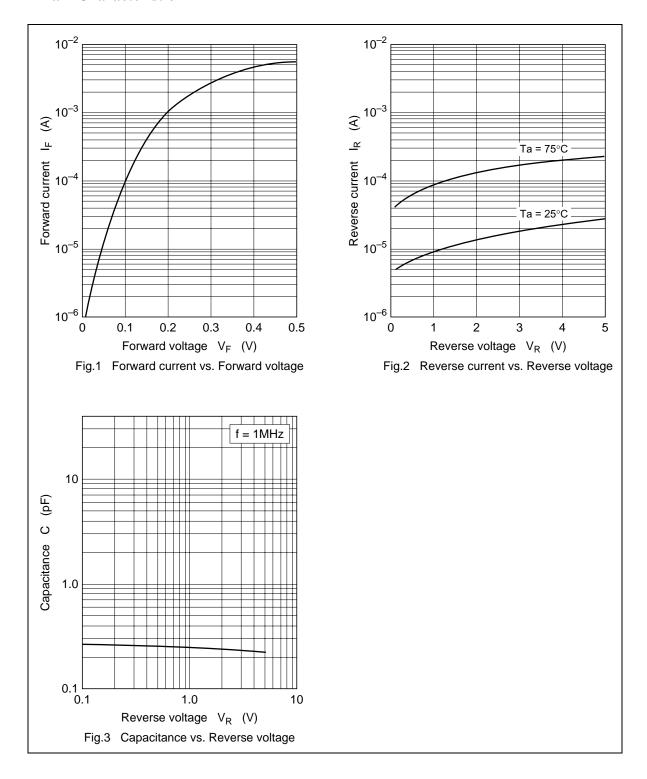
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

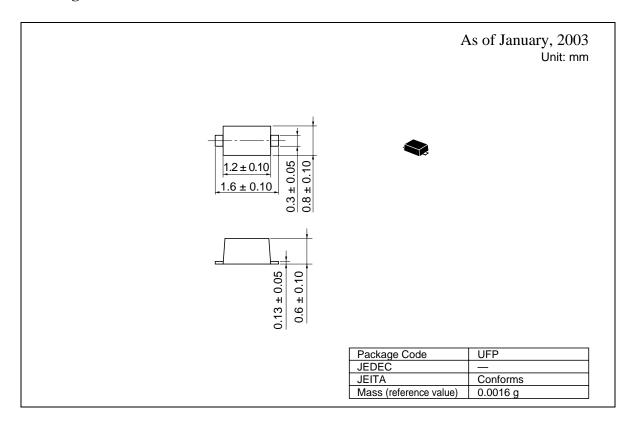
Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V _{F1}	_	_	0.15	V	I _F = 0.1 mA
	V _{F2}	_		0.27		I _F = 1 mA
Capacitance	С	_	0.3	_	рF	V _R = 1 V, f = 1 MHz
ESD-Capability *1	_	10	_	_	V	C = 200 pF, $R_L = 0 \Omega$, Both forward and reverse direction 1 pulse.

Note: 1. Failure criterion; $I_R > 100 \mu A$ at $V_R = 0.5 V$

Main Characteristic



Package Dimensions



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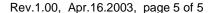
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